

### INCHANGE SEMICONDUCTOR

## Isc N-Channel MOSFET Transistor

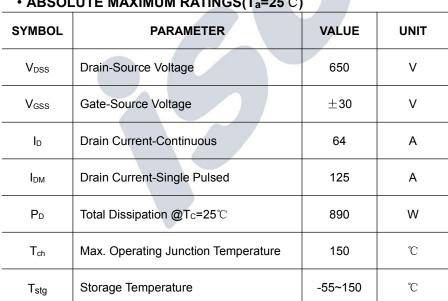
# **IXTH64N65X**

### • FEATURES

- · With TO-247 package
- · Low input capacitance and gate charge
- · Low gate input resistance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### APPLICATIONS

Switching applications

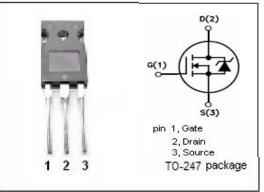


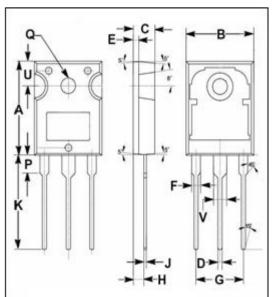
### • ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

#### THERMAL CHARACTERISTICS

| SYMBOL    | PARAMETER                             |      | UNIT |  |
|-----------|---------------------------------------|------|------|--|
| Rth(ch-c) | Channel-to-case thermal resistance    | 3.2  | °C/W |  |
| Rth(ch-a) | Channel-to-ambient thermal resistance | 62.5 | °C/W |  |

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|     | mm    |       |  |  |
|-----|-------|-------|--|--|
| DIM | MIN   | MAX   |  |  |
| Α   | 19.80 | 20.20 |  |  |
| В   | 15.40 | 15.80 |  |  |
| С   | 4.90  | 5.10  |  |  |
| D   | 0.90  | 1.10  |  |  |
| E   | 1.40  | 1.60  |  |  |
| F   | 1.90  | 2.10  |  |  |
| G   | 10.80 | 11.00 |  |  |
| Η   | 2.40  | 2.60  |  |  |
| J   | 0.50  | 0.70  |  |  |
| K   | 19.50 | 20.50 |  |  |
| Ρ   | 3.90  | 4.10  |  |  |
| Q   | 3.30  | 3.50  |  |  |
| U   | 5.20  | 5.40  |  |  |
| V   | 2.90  | 3.10  |  |  |

### isc website: www.iscsemi.cn



# **Isc N-Channel MOSFET Transistor**

# IXTH64N65X

#### **ELECTRICAL CHARACTERISTICS**

#### $T_{C}\text{=}25^{\circ}\!\!\!\!\mathrm{C}$ unless otherwise specified

| SYMBOL               | PARAMETER                      | CONDITIONS  | MIN | ТҮР | MAX       | UNIT |
|----------------------|--------------------------------|---|-----|-----|-----------|------|
| BV <sub>DSS</sub>    | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> =1mA                        | 650 |     |           | V    |
| V <sub>GS</sub> (th) | Gate Threshold Voltage         | V <sub>DS</sub> = ±30V; I <sub>D</sub> =0.25mA                  | 3.0 |     | 5.0       | V    |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance     | V <sub>GS</sub> = 10V; I <sub>D</sub> =32A                      |     |     | 51        | mΩ   |
| I <sub>GSS</sub>     | Gate-Source Leakage Current    | V <sub>GS</sub> = ±30V;V <sub>DS</sub> =0V                      |     |     | ±0.1      | μ Α  |
| I <sub>DSS</sub>     | Drain-Source Leakage Current   | V <sub>DS</sub> = 650V; V <sub>GS</sub> = 0V; TJ=25℃<br>TJ=125℃ |     |     | 10<br>100 | μ Α  |
| V <sub>SDF</sub>     | Diode forward voltage          | I <sub>SD</sub> =64A, V <sub>GS</sub> = 0 V                     |     |     | 1.4       | v    |

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